Manijeh Razeghi

List of Publications by Citations

323 papers	12,755 citations	61 h-index	94 g-index
355 ext. papers	14,297 ext. citations	3.5 avg, IF	6.48 L-index

#	Paper	IF	Citations
323	Semiconductor ultraviolet detectors. *Journal of Applied Physics*, **1996**, 79, 7433-7473	2.5	1159
322	Room temperature quantum cascade lasers with 27% wall plug efficiency. *Applied Physics Letters*, **2011**, 98, 181102	3.4	228
321	Short-wavelength solar-blind detectors-status, prospects, and markets. *Proceedings of the IEEE*, **2002**, 90, 1006-1014	14.3	211
320	Dark current suppression in type II InAs□GaSb superlattice long wavelength infrared photodiodes with M-structure barrier. *Applied Physics Letters*, **2007**, 91, 163511	3.4	181
319	Electroluminescence at 375nm from a ZnO□GaN:Mg□-Al2O3 heterojunction light emitting diode. *Applied Physics Letters*, **2006**, 88, 141918	3.4	159
318	High quality AIN and GaN epilayers grown on (00?1) sapphire, (100), and (111) silicon substrates. *Applied Physics Letters*, **1995**, 66, 2958-2960	3.4	156
317	High-speed, low-noise metal□semiconductor□metal ultraviolet photodetectors based on GaN. *Applied Physics Letters*, **1999**, 74, 762-764	3.4	155
316	High-power 280 nm AlGaN light-emitting diodes based on an asymmetric single-quantum well. *Applied Physics Letters*, **2004**, 84, 1046-1048	3.4	150
315	Solar-blind AlGaN photodiodes with very low cutoff wavelength. *Applied Physics Letters*, **2000**, 76, 403-405	3.4	147
314	Growth and characterization of InGaAs/InGaP quantum dots for midinfrared photoconductive detector. *Applied Physics Letters*, **1998**, 73, 963-965	3.4	136
313	High-performance InAs quantum-dot infrared photodetectors grown on InP substrate operating at room temperature. *Applied Physics Letters*, **2007**, 90, 131112	3.4	132
312	High-quality visible-blind AlGaN p-i-n photodiodes. *Applied Physics Letters*, **1999**, 74, 1171-1173	3.4	131
311	Modeling of type-II InAs/GaSb superlattices using an empirical tight-binding method and interface engineering. *Physical Review B*, **2004**, 69,	3.3	122
310	High-temperature, high-power, continuous-wave operation of buried heterostructure quantum-cascade lasers. *Applied Physics Letters*, **2004**, 84, 314-316	3.4	119
309	Quantum cascade lasers: from tool to product. *Optics Express*, **2015**, 23, 8462-75	3.3	117
308	4.5 mW operation of AlGaN-based 267 nm deep-ultraviolet light-emitting diodes. *Applied Physics Letters*, **2003**, 83, 4701-4703	3.4	115
307	Type II InAs/GaSb superlattice photovoltaic detectors with cutoff wavelength approaching 32 □m. *Applied Physics Letters*, **2002**, 81, 3675-3677	3.4	110

306	Advanced InAs/GaSb superlattice photovoltaic detectors for very long wavelength infrared applications. *Applied Physics Letters*, **2002**, 80, 3262-3264	3.4	109
305	AlxGa1-xN-based back-illuminated solar-blind photodetectors with external quantum efficiency of 89%. *Applied Physics Letters*, **2013**, 103, 191108	3.4	107
304	High quantum efficiency AlGaN solar-blind p-i-n photodiodes. *Applied Physics Letters*, **2004**, 84, 1248-1250	3.4	105
303	Quantum cascade lasers that emit more light than heat. *Nature Photonics*, **2010**, 4, 99-102	33.9	104
302	High-Performance InP-Based Mid-IR Quantum Cascade Lasers. *IEEE Journal of Selected Topics in Quantum Electronics*, **2009**, 15, 941-951	3.8	103
301	AlxGa1□N (0?x?1) ultraviolet photodetectors grown on sapphire by metal-organic chemical-vapor deposition. *Applied Physics Letters*, **1997**, 70, 949-951	3.4	102
300	Interface-induced suppression of the Auger recombination in type-II InAs/GaSb superlattices. *Physical Review B*, **1998**, 58, 15378-15380	3.3	99
299	Visible blind GaN p-i-n photodiodes. *Applied Physics Letters*, **1998**, 72, 3303-3305	3.4	98
298	Two-dimensional electron gas in a In0.53Ga0.47As-InP heterojunction grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **1982**, 40, 877-879	3.4	98
297	A crystallographic model of (00?1) aluminum nitride epitaxial thin film growth on (00?1) sapphire substrate. *Journal of Applied Physics*, **1994**, 75, 3964-3967	2.5	92
296	Uncooled operation of type-II InAs□GaSb superlattice photodiodes in the midwavelength infrared range. *Applied Physics Letters*, **2005**, 86, 233106	3.4	90
295	High operating temperature midwave infrared photodiodes and focal plane arrays based on type-II InAs/GaSb superlattices. *Applied Physics Letters*, **2011**, 98, 143501	3.4	89
294	Very high quantum efficiency in type-II InAs□GaSb superlattice photodiode with cutoff of 12□m. *Applied Physics Letters*, **2007**, 90, 231108	3.4	89
293	2.4 W room temperature continuous wave operation of distributed feedback quantum cascade lasers. *Applied Physics Letters*, **2011**, 98, 181106	3.4	88
292	High quality aluminum nitride epitaxial layers grown on sapphire substrates. *Applied Physics Letters*, **1994**, 64, 339-341	3.4	87
291	Top-emission ultraviolet light-emitting diodes with peak emission at 280 nm. *Applied Physics Letters* , **2002**, 81, 801-802	3.4	86
290	InAs/InAs1□Sbx type-II superlattices for high performance long wavelength infrared detection. *Applied Physics Letters*, **2014**, 105, 121104	3.4	85
289	Growth of AlxGa1□N:Ge on sapphire and silicon substrates. *Applied Physics Letters*, **1995**, 67, 1745-1747	3.4	84

288	Hole-initiated multiplication in back-illuminated GaN avalanche photodiodes. *Applied Physics Letters*, **2007**, 90, 141112	3.4	83
287	Avalanche multiplication in AlGaN based solar-blind photodetectors. *Applied Physics Letters*, **2005**, 87, 241123	3.4	83
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285	Use of ZnO thin films as sacrificial templates for metal organic vapor phase epitaxy and chemical lift-off of GaN. *Applied Physics Letters*, **2007**, 91, 071120	3.4	81
284	Advances in mid-infrared detection and imaging: a key issues review. *Reports on Progress in Physics*, **2014**, 77, 082401	14.4	80
283	Demonstration of shortwavelength infrared photodiodes based on type-II InAs/GaSb/AlSb superlattices. *Applied Physics Letters*, **2012**, 100, 211101	3.4	80
282	Band-gap narrowing and potential fluctuation in Si-doped GaN. *Applied Physics Letters*, **1999**, 74, 102-104	3.4	80
281	Near bulk-limited R0A of long-wavelength infrared type-II InAs□GaSb superlattice photodiodes with polyimide surface passivation. *Applied Physics Letters*, **2007**, 90, 233513	3.4	79
280	Ammonium sulfide passivation of Type-II InAs/GaSb superlattice photodiodes. *Applied Physics Letters*, **2004**, 84, 2037-2039	3.4	79
279	Crystallography of epitaxial growth of wurtzite-type thin films on sapphire substrates. *Journal of Applied Physics*, **1994**, 75, 4515-4519	2.5	79
278	AlN/GaN double-barrier resonant tunneling diodes grown by metal-organic chemical vapor deposition. *Applied Physics Letters*, **2010**, 96, 042103	3.4	76
277	Growth and characterization of InAs/GaSb photoconductors for long wavelength infrared range. *Applied Physics Letters*, **1997**, 71, 1403-1405	3.4	74
276	Minority electron unipolar photodetectors based on type II InAs/GaSb/AlSb superlattices for very long wavelength infrared detection. *Applied Physics Letters*, **2009**, 95, 183502	3.4	72
275	Background limited long wavelength infrared type-II InAs/GaSb superlattice photodiodes operating at 110 K. *Applied Physics Letters*, **2008**, 93, 123502	3.4	70
274	Demonstration of a 256□256 middle-wavelength infrared focal plane array based on InGaAs/InGaP quantum dot infrared photodetectors. *Applied Physics Letters*, **2004**, 84, 2232-2234	3.4	68
273	High-power continuous-wave operation of a 6 □m quantum-cascade laser at room temperature. *Applied Physics Letters*, **2003**, 83, 2503-2505	3.4	66
272	Kinetics of photoconductivity in n-type GaN photodetector. *Applied Physics Letters*, **1995**, 67, 3792-3794	3.4	66
271	Comparison of the physical properties of GaN thin films deposited on (0001) and (011 2) sapphire substrates. *Applied Physics Letters*, **1993**, 63, 973-975	3.4	66

270	Surface plasmon enhanced light emission from AlGaN-based ultraviolet light-emitting diodes grown on Si (111). *Applied Physics Letters*, **2013**, 102, 211110	3.4	65
269	Lateral epitaxial overgrowth of GaN films on sapphire and silicon substrates. *Applied Physics Letters*, **1999**, 74, 570-572	3.4	65
268	Reliability in room-temperature negative differential resistance characteristics of low-aluminum content AlGaN/GaN double-barrier resonant tunneling diodes. *Applied Physics Letters*, **2010**, 97, 181109	3.4	64
267	High performance bias-selectable three-color Short-wave/Mid-wave/Long-wave Infrared Photodetectors based on Type-II InAs/GaSb/AlSb superlattices. *Scientific Reports*, **2016**, 6, 24144	4.9	63
266	Continuous operation of a monolithic semiconductor terahertz source at room temperature. *Applied Physics Letters*, **2014**, 104, 221105	3.4	62
265	Bias-selectable dual-band mid-/long-wavelength infrared photodetectors based on InAs/InAs1□Sbx type-II superlattices. *Applied Physics Letters*, **2015**, 106, 011104	3.4	62
264	Photoluminescence study of AlGaN-based 280 nm ultraviolet light-emitting diodes. *Applied Physics Letters*, **2003**, 83, 4083-4085	3.4	62
263	Room temperature single-mode terahertz sources based on intracavity difference-frequency generation in quantum cascade lasers. *Applied Physics Letters*, **2011**, 99, 131106	3.4	61
262	Passivation of type-II InAs□GaSb double heterostructure. *Applied Physics Letters*, **2007**, 91, 091112	3.4	61
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258	High performance photodiodes based on InAs/InAsSb type-II superlattices for very long wavelength infrared detection. *Applied Physics Letters*, **2014**, 104, 251105	3.4	58
257	High power, continuous wave, room temperature operation of □~ 3.4 □m and □~ 3.55 □m InP-based quantum cascade lasers. *Applied Physics Letters*, **2012**, 100, 212104	3.4	58
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255	Passivation of type II InAs/GaSb superlattice photodiodes. *Thin Solid Films*, **2004**, 447-448, 489-492	2.2	58
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250	Pulse autocorrelation measurements based on two- and three-photon conductivity in a GaN photodiode. *Applied Physics Letters*, **1999**, 75, 3778-3780	3.4	55
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246	320×256 solar-blind focal plane arrays based on AlxGa1−xN. *Applied Physics Letters*, **2005**, 86, 011117	3.4	54
245	Aluminum gallium nitride short-period superlattices doped with magnesium. *Applied Physics Letters* , **1999**, 74, 2023-2025	3.4	54
244	Widely tunable room temperature semiconductor terahertz source. *Applied Physics Letters*, **2014**, 105, 201102	3.4	53
243	Watt level performance of quantum cascade lasers in room temperature continuous wave operation at ~3.76 μm. *Applied Physics Letters*, **2010**, 97, 131117	3.4	53
242	Advances in antimonide-based Type-II superlattices for infrared detection and imaging at center for quantum devices. *Infrared Physics and Technology*, **2013**, 59, 41-52	2.7	52
241	Growth and Characterization of Long-Wavelength Infrared Type-II Superlattice Photodiodes on a 3-in GaSb Wafer. *IEEE Journal of Quantum Electronics*, **2011**, 47, 686-690	2	52
240	A hybrid green light-emitting diode comprised of n-ZnO/(InGaN/GaN) multi-quantum-wells/p-GaN. *Applied Physics Letters*, **2008**, 93, 081111	3.4	52
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236	Growth and characterization of InSbBi for long wavelength infrared photodetectors. *Applied Physics Letters*, **1997**, 70, 3266-3268	3.4	49
235	Very long wavelength infrared type-II detectors operating at 80 K. *Applied Physics Letters*, **2000**, 77, 1572-1574	3.4	49

234	Demonstration of midinfrared type-II InAs/GaSb superlattice photodiodes grown on GaAs substrate. *Applied Physics Letters*, **2009**, 94, 223506	3.4	44
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232	Widely tuned room temperature terahertz quantum cascade laser sources based on difference-frequency generation. *Applied Physics Letters*, **2012**, 101, 251121	3.4	43
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227	Near milliwatt power AlGaN-based ultraviolet light emitting diodes based on lateral epitaxial overgrowth of AlN on Si(111). *Applied Physics Letters*, **2013**, 102, 011106	3.4	41
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219	Geiger-mode operation of ultraviolet avalanche photodiodes grown on sapphire and free-standing GaN substrates. *Applied Physics Letters*, **2010**, 96, 261107	3.4	39
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217	Study of Au coated ZnO nanoarrays for surface enhanced Raman scattering chemical sensing. *Journal of Materials Chemistry C*, **2017**, 5, 3528-3535	7.1	38

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213	Very high purity InP epilayer grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **1988**, 52, 117-119	3.4	38
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170	High Operability 1024$,times,$1024 Long Wavelength Type-II Superlattice Focal Plane Array. *IEEE Journal of Quantum Electronics*, **2012**, 48, 221-228	2	26
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167	High-average-power, high-duty-cycle (□6 □n) quantum cascade lasers. *Applied Physics Letters*, **2002**, 81, 4321-4323	3.4	26
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